

REMARKS

Claims 1, 6, 7, 9, 11, and 15 have been amended herein. Upon entry of this amendment, claims 1-4, 6-16 will be pending in the above-identified application.

Applicant acknowledges the allowance of claims 1-4, 7, 8, 10, and 12-15.

Claim 11

Applicant respectfully requests reconsideration of the rejection of claim 11 under 35 U.S.C. § 112, second paragraph, as being indefinite. Claim 11 has been amended to remove "FLARE" and "SILK." Accordingly, the rejection is improper and Applicant requests the rejection be withdrawn.

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Claims 6, 9, and 16

Applicant respectfully requests reconsideration of the rejection of claims 6, 9 and 16 under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,514,868 (Hui). As amended, claims 6 and 16 recite a method of manufacturing a semiconductor apparatus comprising, among other things, providing a film to be processed on a substrate, providing at least one dielectric mask material film on the film to be processed, wherein the dielectric mask material has a dielectric constant lower than silicon dioxide and a heatproof temperature of about 350 degrees Centigrade, and providing a resist film on the at least one dielectric mask material film.

Hui discloses a method of creating integrated circuits including an anti-reflective coating layer 26 made of silicon nitride or silicon oxynitride. Hui does not disclose a dielectric mask material film disposed on a film to be processed wherein the dielectric mask material has a dielectric constant lower than silicon dioxide and a heatproof temperature of about 350 degrees Centigrade. The claimed dielectric constant and heatproof temperature qualities are characteristic of organic materials FLARE and SILK (See page 4, line 24 to page 5, line 6 of the present specification).

Claim 9, as amended, recites a method of reducing a contact hole diameter in a semiconductor apparatus comprising, among other things, providing a film to be processed on a substrate, wherein the film to be processed has a step, and disposing at least one dielectric mask material film on the film to be processed such that the at least

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one dielectric mask material film planarizes an unevenness created by the step. Hui does not show providing a film to be processed having a step and disposing at least one dielectric mask material film on the film to be processed such that the at least one dielectric mask material film planarizes an unevenness created by the step.

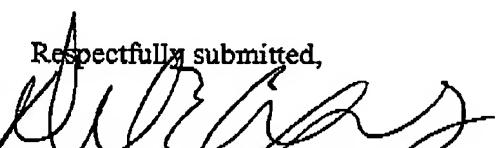
Because the reference fails to show every feature of claims 6, 9, and 16, the rejection is improper. Accordingly, Applicant respectfully requests the rejection be withdrawn.

Conclusion

As it is believed that the application is in condition for allowance, favorable action and a Notice of Allowance are respectfully requested.

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Respectfully submitted,


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